



Using Machine Learning to Enhance Flash Endurance & Latency

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Challenges in Error Recovery

- During SSD Service Time:
 - P/E Cycle, Data Retention, Read Disturb
 - Critical R/W Condition(Temperature)
- Decoding Strategy:
 - Read Retry
 - Soft Decoding
 - ...
- Challenges:
 - Keep High Reliability & Low Latency under Variant Operation Condition





Input Parameters:

- Some factors will affect NAND Flash Status. (P/E Cycle, Retention Time, Read Count, Temperature...)
- Some information from NAND Flash are also collected as Input Parameters (Program/Erase Time, ...)

Status Prediction:

- Our target is to predict NAND Flash Status (Ex: Optimal Read Level, Error Recovery Flow) by Input Parameters.





Optimal Decoding Parameters

Example : Binary LDPC - MSA

1. Read Level for Hard Bit → Minimize Error Bits

2. Read Level for Soft Bit & LLR Value → Maximize the Decoding Capability

• Optimal Read Level & LLR Prediction

- Maximize Decoding Capability. Extend the Endurance
- Vary with Operation Condition (P/E Cycle, Retention Time, Read Count, Temperature...)

Memory Error Recovery Flow - Prediction



- Error Recovery Flow Prediction
 - Throughput/Latency Control, End of Life Prediction



Visual Illustration - Error Recovery Flow







Visual Illustration – Soft Decode







Parameter Optimization with ML

Category	ltem	Description	Remark
P/E	Cycle	0, 1000,~	
	Temperature	(Random)	
	Dwell	(Random)	
Test Item	Data Retention	0, 1, ~ (Days)	Room Temperature
	Data Retention	0, 1, ~ (Days)	High Temperature
	Read Disturb	0, 1000, ~	

- A Smart Error Recovery Scheme is developed by Machine Learning
- This Scheme can be applied to variant operation condition (combination of {PE, DR, RD, Temperature})
- This Scheme can extend the endurance and reduce the latency



Endurance with Hard Decoding



- Our Error Recovery Scheme use ML to find Optimal Read Level for variant operation conditions (combination of {PE, DR, RD, Temperature})
- 5x Extension for Baking Time & 2x Extension for P/E Count

Memory Endurance with Hard/Soft Decoding



 Proposed Error Recovery Scheme with only Hard Decode is still better than Traditional Read Retry + Soft Decode in Decoding Coverage

Throughput/IOPS Comparison

Flas

Memory

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 Proposed Error Recovery Scheme always has less read latency compared with Traditional Error Recovery Scheme



Throughput with Future Status Prediction



Memory

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 Read Performance Drop can be further reduced with Future Status Prediction



THANK YOU! Any questions?

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